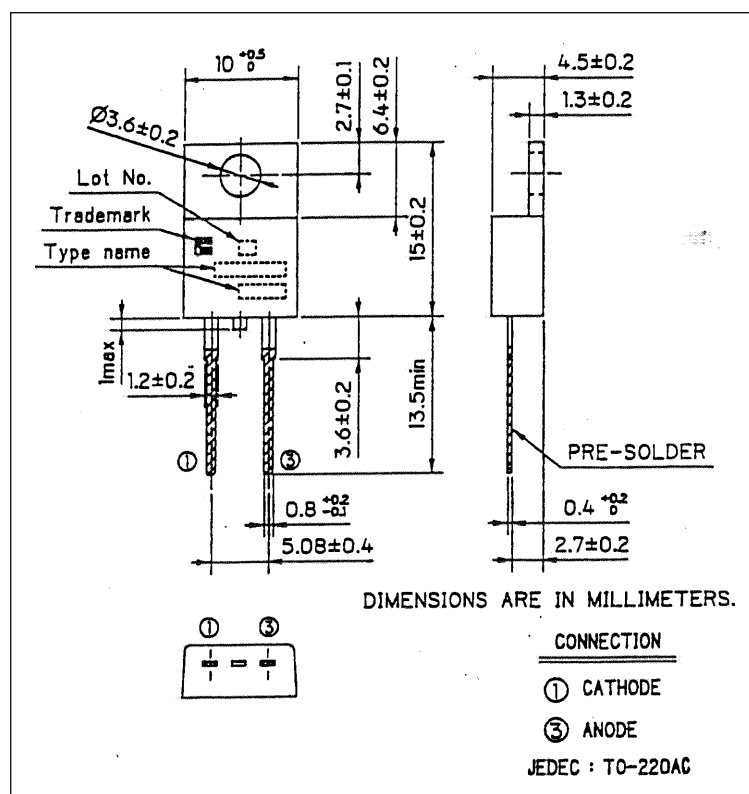
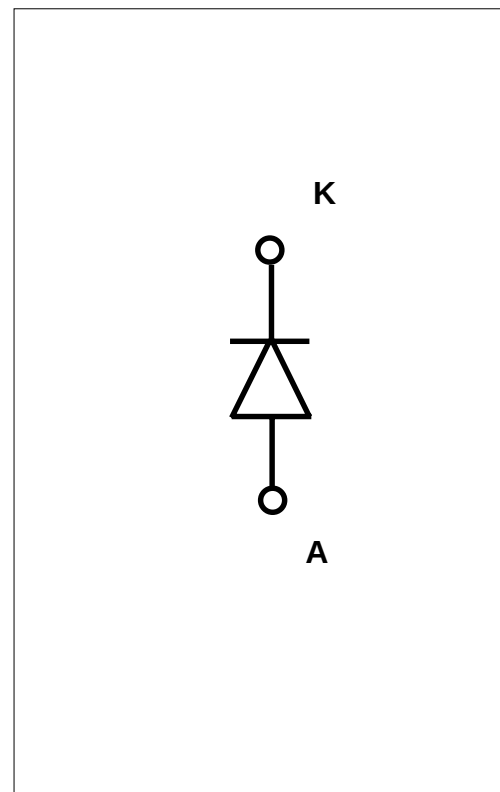


Fast Recovery Diode for IGBT

Outline Drawings Units mm



Equivalent circuit



Maximum ratings and characteristics

Absolute maximum ratings (Tc=25°C)

Item	Symbol	Test Conditions	Ratings	Units
Repetitive Reverse Voltage	V _{RRM}		600	V
Repetitive peak surge current	I _{FM}	20kHz Duty 50% Squ. wave	5	A
		Tc=118°C	13	A
Average rectified forward current	I _{F(A)}	DC	5	A
Non-repetitive peak surge current	I _{FSM}	Pulse 10ms, sin. wave	40	A
Maximam Power Dissipaion	P _o		25	W
Operating Temperature	T _j		+150	°C
Storage Temperature	T _{stg}		-40 to +150	°C
Mounting Screw Torque			50	N·cm

Electrical characteristics (at Tc=25°C unless otherwise specified)

Item	Symbol	Test Conditions	Max	Units
Reverse Current	I _R	V _R = 600V	1.0	mA
Foward voltage	V _{FM}	I _F = 5A	3.0	V
Reverse recovery time	t _{rr}	I _F = 5A, V _R =200V, di/dt=100A/μs	0.3	μs

Thermal resistance characteristics

Item	Symbol	Test Conditions	Max	Units
Thermal resistance	R _{th(j-c)}	junction to case	5.0	°C/W

■ Characteristics

